

D40C4
NPN SILICON
DARLINGTON POWER
TRANSISTOR



TO-202 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR D40C4 type is an NPN silicon Darlington power transistor designed for general purpose amplifier applications where high gain is required.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

Collector-Emitter Voltage	
Collector-Emitter Voltage	
Emitter-Base Voltage	
Continuous Collector Current	
Peak Collector Current	
Power Dissipation	
Operating and Storage Junction Temperature	
Thermal Resistance	

SYMBOL		UNITS
V_{CES}	40	V
V_{CEO}	40	V
V_{EBO}	13	V
I_C	0.5	A
I_{CM}	1.0	A
P_D	6.25	W
T_J, T_{stg}	-55 to +150	$^\circ\text{C}$
Θ_{JC}	20	$^\circ\text{C/W}$

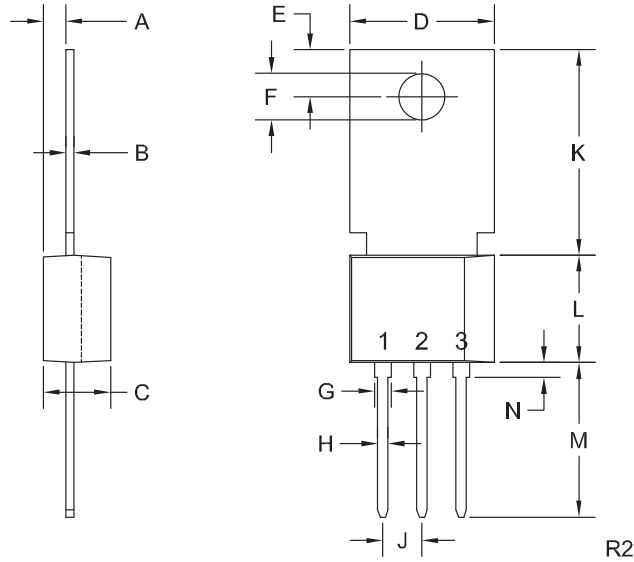
ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I_{CES}	$V_{CE}=40\text{V}$			500	nA
I_{CBO}	$V_{CE}=40\text{V}, T_C=150^\circ\text{C}$			20	μA
I_{EBO}	$V_{EB}=13\text{V}$			100	nA
BV_{CEO}	$I_C=10\text{mA}$	40			V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=0.5\text{mA}$			1.5	V
$V_{BE(SAT)}$	$I_C=500\text{mA}, I_B=0.5\text{mA}$			2.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=200\text{mA}$	10K		70K	
f_T	$V_{CE}=5.0\text{V}, I_C=20\text{mA}$		80		MHz
C_{cb}	$V_{CB}=10\text{V}, f=1.0\text{MHz}$			10	pF
t_{on}	$I_C=1.0\text{A}, I_{B1}=1.0\text{mA}$		120		ns
t_{off}	$I_C=1.0\text{A}, I_{B1}=I_{B2}=1.0\text{mA}$		1200		ns

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TO-202 CASE - MECHANICAL OUTLINE



LEAD CODE:
1) Emitter
2) Base
3) Collector
Tab is common to pin 3

MARKING:
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SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.055	0.071	1.40	1.80
B	0.016	0.024	0.40	0.60
C	0.173	0.181	4.40	4.60
D	0.374	0.413	9.50	10.5
E	0.118	0.154	3.00	3.90
F (DIA)	0.124	0.150	3.15	3.80
G	0.035	0.055	0.90	1.40
H	0.023	0.031	0.59	0.80
J	0.094	0.106	2.39	2.69
K	0.459	0.559	11.66	14.21
L	0.280	0.346	7.12	8.80
M	0.406	0.531	10.3	13.5
N	0.024	0.059	0.60	1.50

TO-202 (REV: R2)

R1 (23-January 2012)